

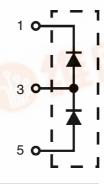
Advanced Technical Information

Dual HiPerFRED™ **Epitaxial Diode**

DSEE 55-24N1F

= 2400 V= 55 A







Rectifier Bridge				
Symbol	Conditions	Maximum F	laximum Ratings	
V _{RRM} ① V _{RRM}		2400 1200	V V	
I _{FAV} I _{F(AV)M} I _{FSM}	$T_c = 90^{\circ}\text{C}$; sine 180° $T_c = 90^{\circ}\text{C}$; d = 0.5 rectangular $T_{\text{VJ}} = 25^{\circ}\text{C}$; t = 10 ms; sine 50 Hz	53 55 500	A A A	
E _{AS}	I_{AS} = 16 A; L_{AS} = 180 μ H; T_{C} = 25°C; non repetitive	e 28	mJ	
P _{tot}	T _C = 25°C (per diode)	200	W	

	2400	V
	1200	V
T _C = 90°C; sine 180°	53	Α
$T_c = 90^{\circ}C$; d = 0.5 rectangular	55	Α
$T_{VJ} = 25^{\circ}C; t = 10 \text{ ms}; \text{ sine } 50 \text{ Hz}$	500	Α
$I_{AS} = 16 \text{ A}$; $L_{AS} = 180 \mu\text{H}$; $T_{C} = 25^{\circ}\text{C}$; non repetitive	28	mJ
$T_c = 25$ °C (per diode)	200	W
(
	$T_{C} = 90^{\circ}\text{C}$; d = 0.5 rectangular $T_{VJ} = 25^{\circ}\text{C}$; t = 10 ms; sine 50 Hz $I_{AS} = 16 \text{ A}$; $I_{AS} = 180 \mu\text{H}$; $I_{C} = 25^{\circ}\text{C}$; non repetitive	$T_{\rm C} = 90^{\circ}$ C; sine 180° 53 $T_{\rm C} = 90^{\circ}$ C; d = 0.5 rectangular 55 $T_{\rm VJ} = 25^{\circ}$ C; t = 10 ms; sine 50 Hz 500 $I_{\rm AS} = 16$ A; $L_{\rm AS} = 180$ μH; $T_{\rm C} = 25^{\circ}$ C; non repetitive 28

Symbol	Conditions	Characteristic Values (T _{VJ} = 25°C, unless otherwise specified)			
		min.	typ.	max.	
V _F	$I_F = 40 \text{ A}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	TO COM	2.0 1.5	2.5	V
I _R	$V_{R} = V_{RRM}$, $T_{VJ} = 25^{\circ}C$ $T_{VJ} = 125^{\circ}C$	Lac	1	1	mA mA
I _{RM} t _{rr}	$\begin{cases} I_F = 75 \text{ A; } di_F/dt = -750 \text{ A/µs; T} \\ V_R = 600 \text{ V} \end{cases}$	_{vJ} = 125°C	79 220		A ns
R _{thJC}	(per diode)			0.63	K/W

Data according to IEC 60747 and refer to a single diode unless otherwise stated

① Diodes connected in series

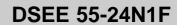
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Features

- HiPerFRED™ Epitaxial Diodes
- fast and soft reverse recovery low switching losses
- avalanche rated
- low leakage current
- ISOPLUS i4-PAC™ package
- isolated back surface
- low coupling capacity between pins and heatsink
- enlarged creepage towards heatsink
- enlarged creepage between pins - application friendly pinout
- high reliability
- industry standard outline

Applications

- · rectifiers
- high frequency rectifiers, output rectifiers of switched mode power supplies
- mains rectifiers with minimized emission of disturbances
- diodes in snubber networks
- high voltage diodes using the series connection in the component





Component					
Symbol	Conditions	Maximum R	Maximum Ratings		
T _{vJ} T _{stg}		-55+150 -55+125	°C		
V _{ISOL}	I _{ISOL} ≤ 1 mA; 50/60 Hz	2500	V~		
F _c	mounting force with clip	20120	N		

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
C _P	coupling capacity between shorted pins and mounting tab in the case		40	pF
d _s , d _A d _s , d _A	pin - pin pin - backside metal	5.5 5.5		mm mm
R _{thCH}	with heatsink compound		0.15	K/W
Weight	·		9	g

